

AMENDMENTS TO THE CLAIMS

Claim 1 (Currently Amended): A resist composition comprising a fluoropolymer (A); an acid-generating compound (B) which generates an acid under irradiation with light; and an organic solvent (C), wherein

the fluoropolymer (A) which is a fluoropolymer having repeating units formed by cyclopolymerization of a fluorinated diene represented by the formula (1)



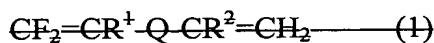
where

each of R¹ and R², which are independent of each other, is a hydrogen atom, a fluorine atom, a methyl group or a trifluoromethyl group;

Q is a bivalent organic group having a blocked acidic group capable of forming an acidic group by an acid or a group which can be converted to such a blocked acidic group;

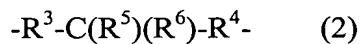
the fluorinated diene and which has blocked acidic groups, provided that ; and in a case where Q is a the bivalent organic group having a group which can be converted to a blocked acidic group, said group is converted to a blocked acidic group after the cyclopolymerization

, an acid generating compound (B) which generates an acid under irradiation with light, and an organic solvent (C);



wherein each of R¹ and R² which are independent of each other, is a hydrogen atom, a fluorine atom, a methyl group or a trifluoromethyl group, and Q is a bivalent organic group having a blocked acidic group capable of forming an acidic group by an acid or a group which can be converted to such a blocked acidic group.

Claim 2 (Currently Amended): The resist composition according to Claim 1, wherein Q is a bivalent organic group represented by the formula (2):



wherein where

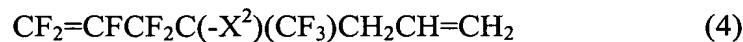
each of R^3 and R^4 , which are independent of each other, is a single bond, an oxygen atom, an alkylene group having at most 3 carbon atoms, which may have an etheric oxygen atom, or a fluoroalkylene group having at most 3 carbon atoms, which may have an etheric oxygen atom, atom;

R^5 is a hydrogen atom, a fluorine atom, an alkyl group having at most 3 carbon atoms or a fluoroalkyl group having at most 3 carbon atoms, atoms; and

R^6 is a blocked acidic group, an acidic group, or a monovalent organic group having a blocked acidic group or an acidic group.

Claim 3 (Original): The resist composition according to Claim 1, wherein the acidic group is an acidic hydroxyl group, and the blocked acidic group is a blocked acidic hydroxyl group.

Claim 4 (Currently Amended): The resist composition according to Claim 1, wherein the fluorinated diene is a fluorinated diene represented by the formula (4) or (5):



wherein where

X² is O(t-C₄H₉), OCH₂OCH₃, OC₂OOC(t-C₄H₉), OCH(CH₃)OC₂H₅ or a 2-tetrahydropyranyloxy group ,and ; and
p is an integer of from 1 to 3.

Claim 5 (Currently Amended) The resist composition according to Claim 1, wherein the fluoropolymer (A) is a copolymer comprising

repeating units formed by cyclopolymerization of a the fluorinated diene represented by the formula (1) and
repeating units formed by polymerization of other monomers ,wherein ; and
the proportion of the repeating units formed by polymerization of other monomers is at most 30 mol%.

Claim 6 (Currently Amended): The A method of using a resist composition, the method comprising exposing the resist composition according to of Claim 1 ,which is a resist composition for exposure by to ultraviolet rays having a wavelength of at most 200 nm.

Claim 7 (Currently Amended): The resist composition method according to Claim 6, wherein the ultraviolet rays having a wavelength of at most 200 nm are in ArF excimer laser beams or F₂ excimer laser beams.

Claim 8 (Currently Amended): A process for forming a pattern, ~~which comprises the~~
process comprising

coating the resist composition ~~as defined in~~ of Claim 1 on a substrate,
then removing the organic solvent (C) to form a thin film of a resist comprising the
fluoropolymer (A) and the acid-generating compound (B), ~~and~~
then irradiating the thin film with ultraviolet rays having a wavelength of at most 200
nm ~~capable of~~,
generating an acid from the acid-generating compound (B) ~~to form a~~, and
forming the pattern.

Claim 9 (Currently Amended): The process according to Claim 8, wherein the
ultraviolet rays having a wavelength of at most 200 nm are in ArF excimer laser beams or F₂
excimer laser beams.